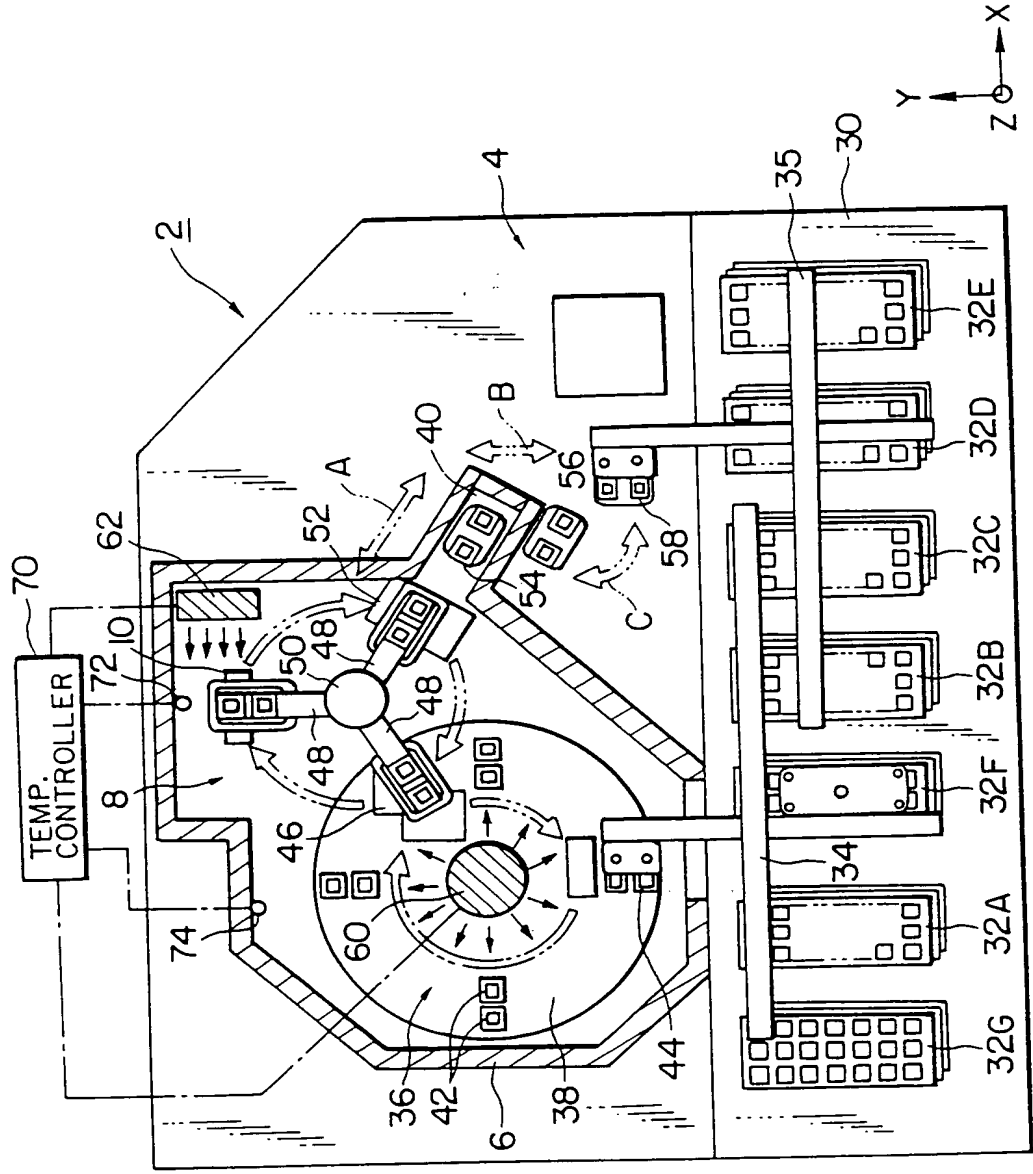


FIG. 1



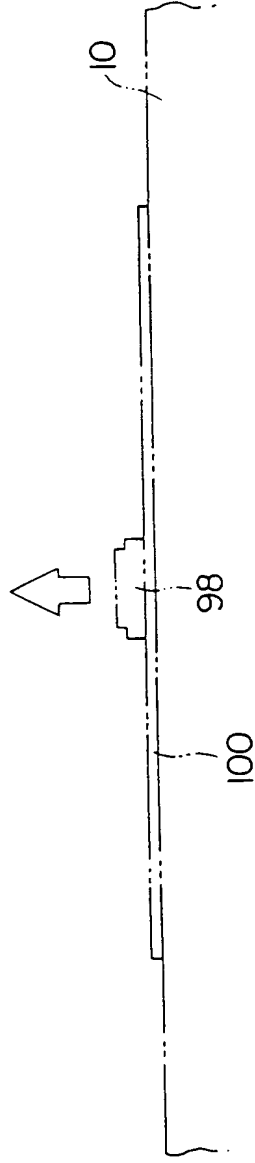


FIG. 3

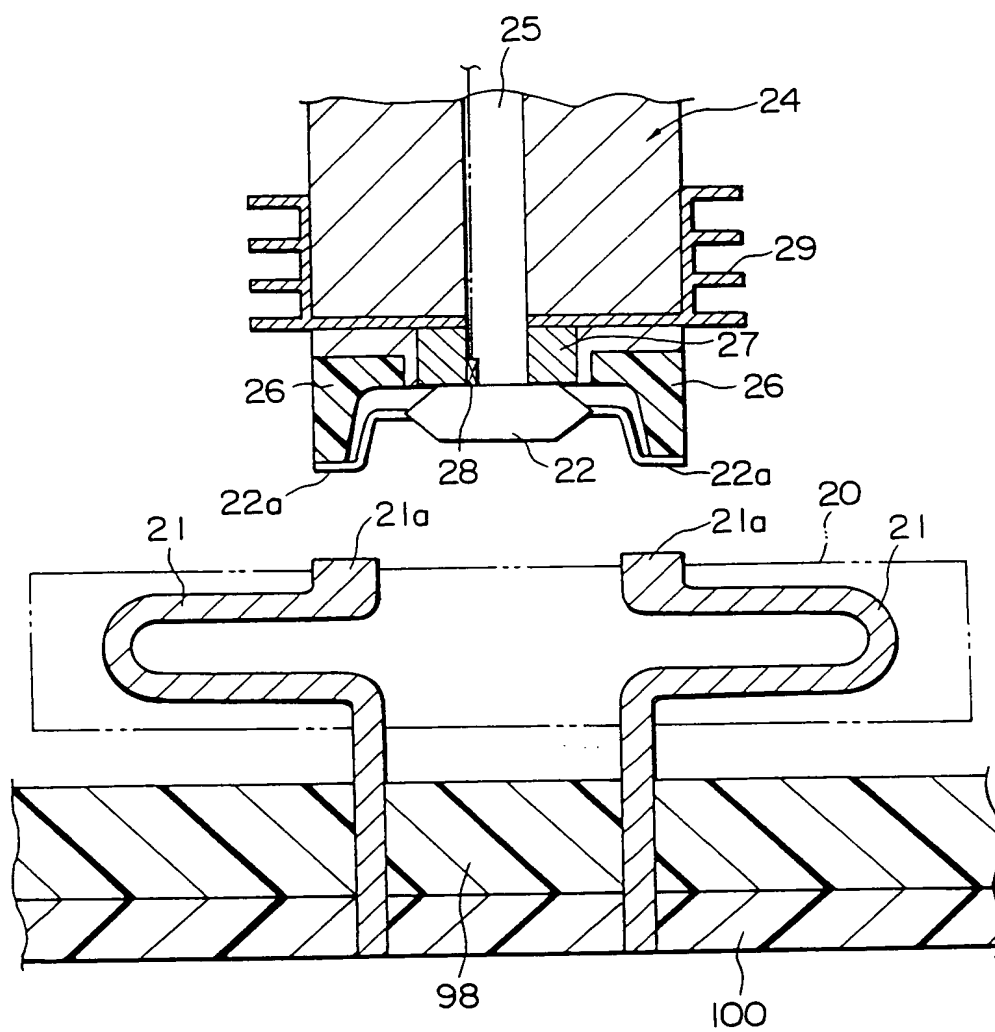


FIG. 4

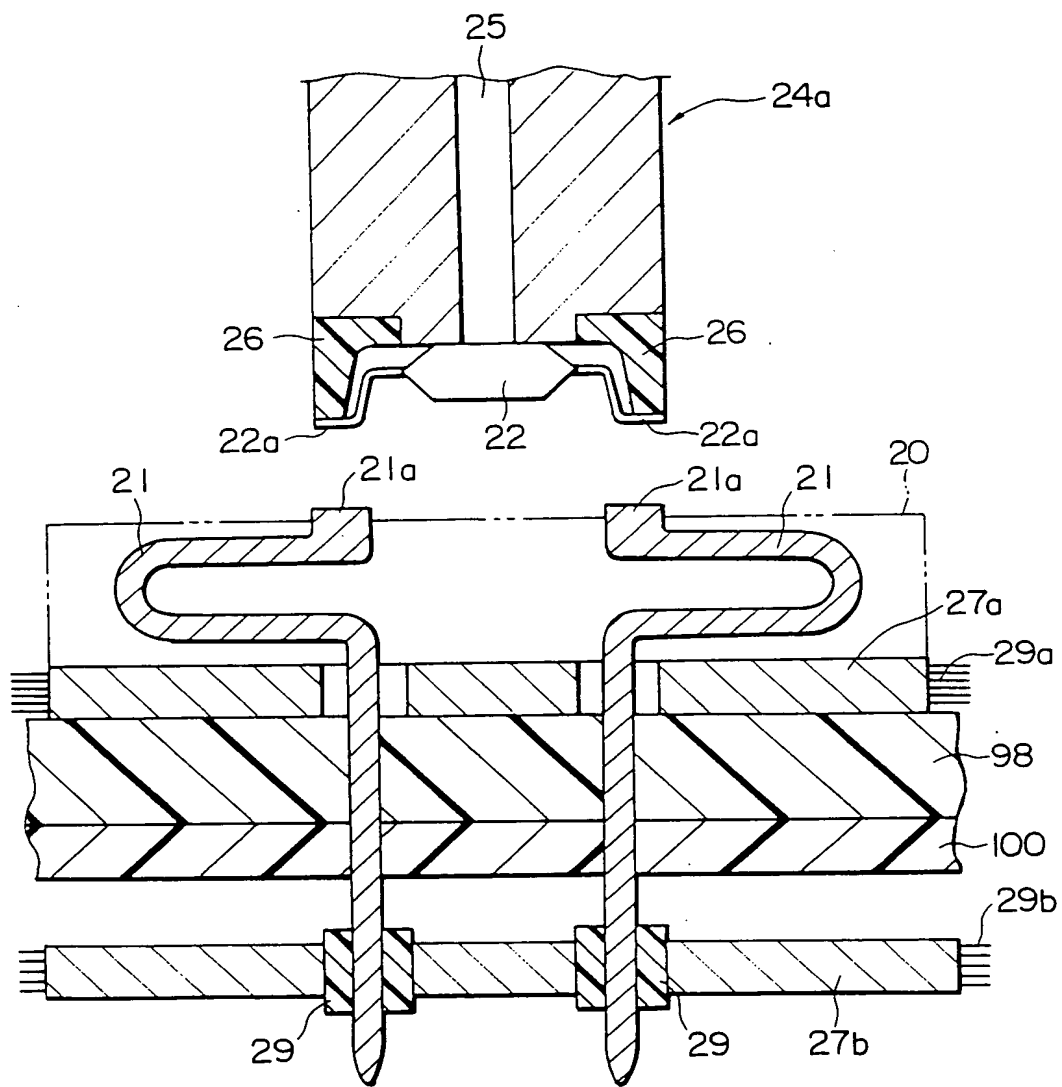


FIG. 5

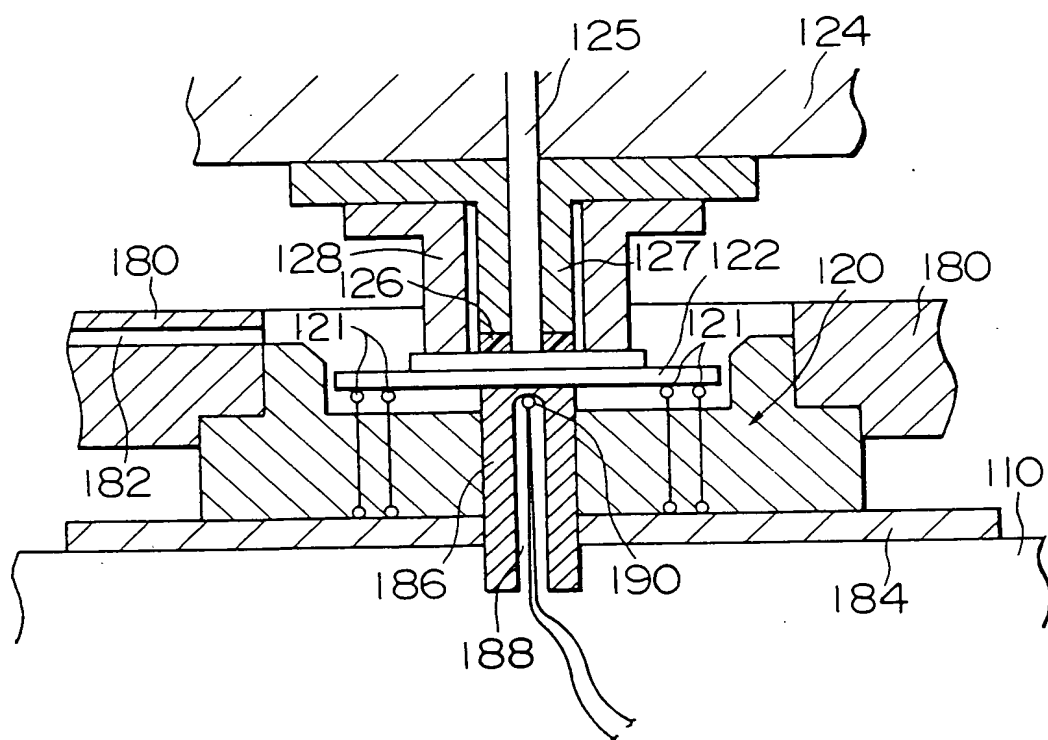


FIG. 6

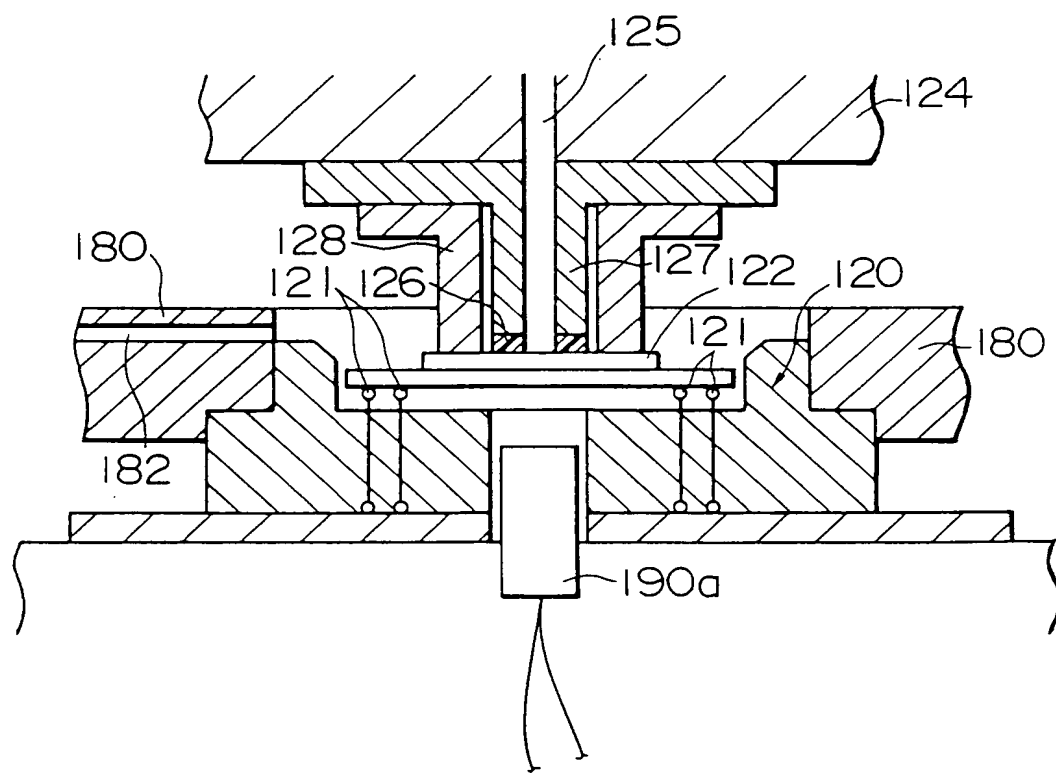


FIG. 7

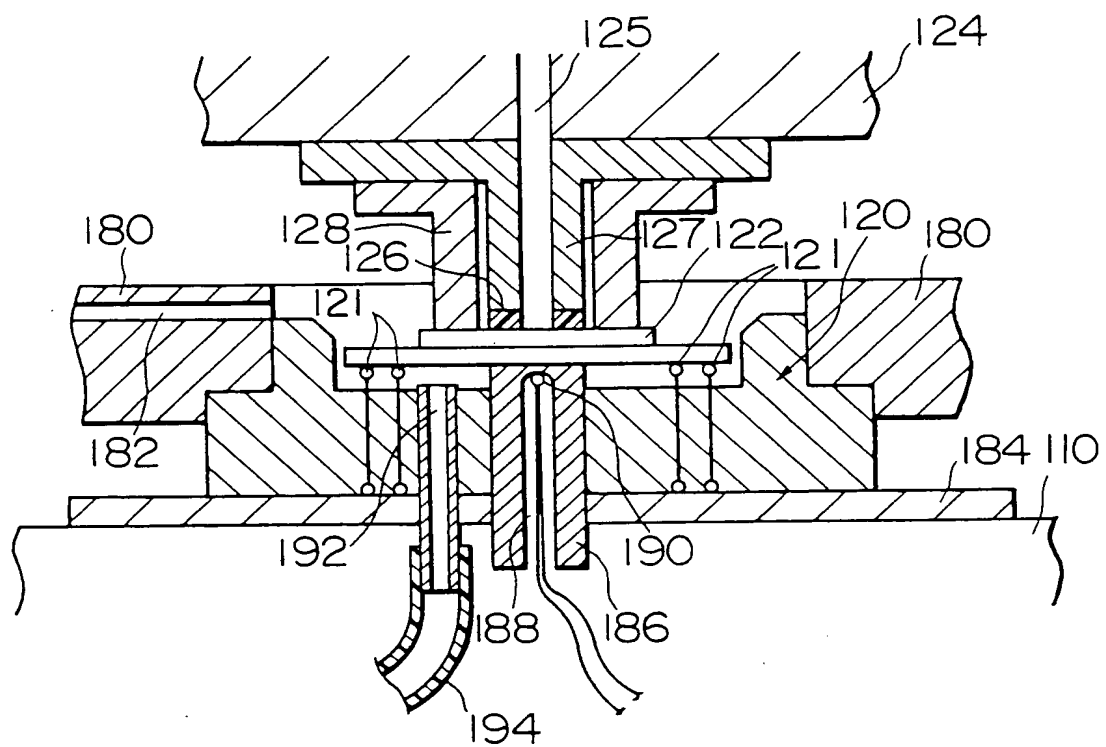


FIG. 8

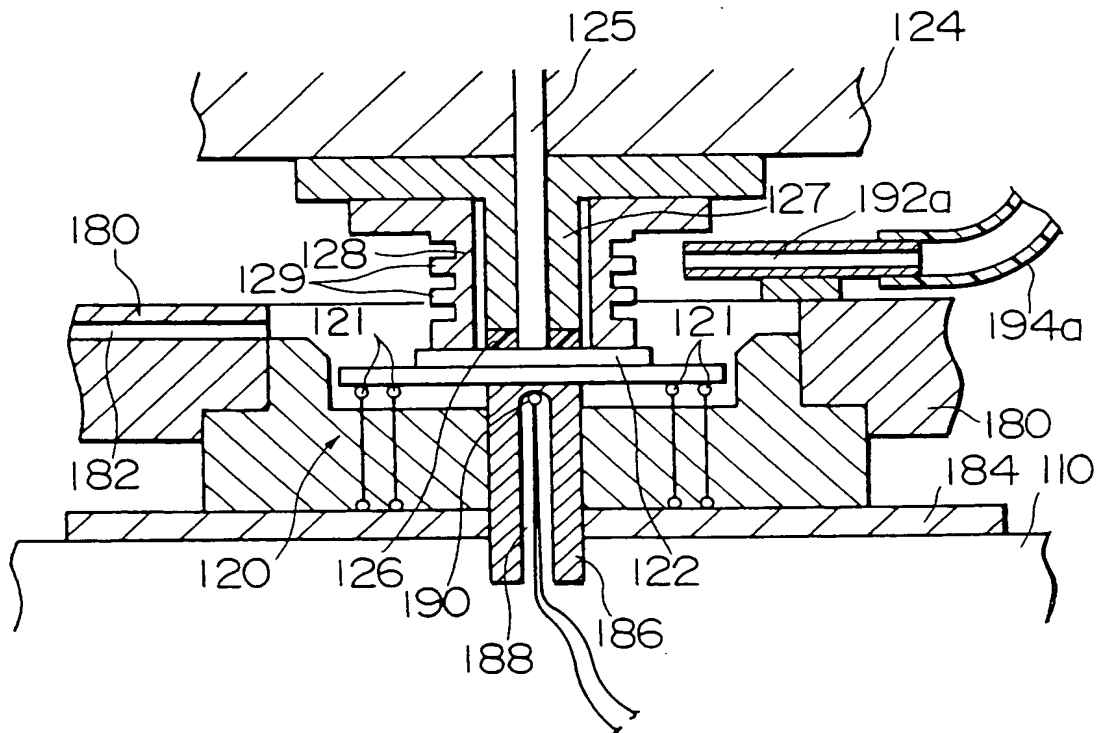
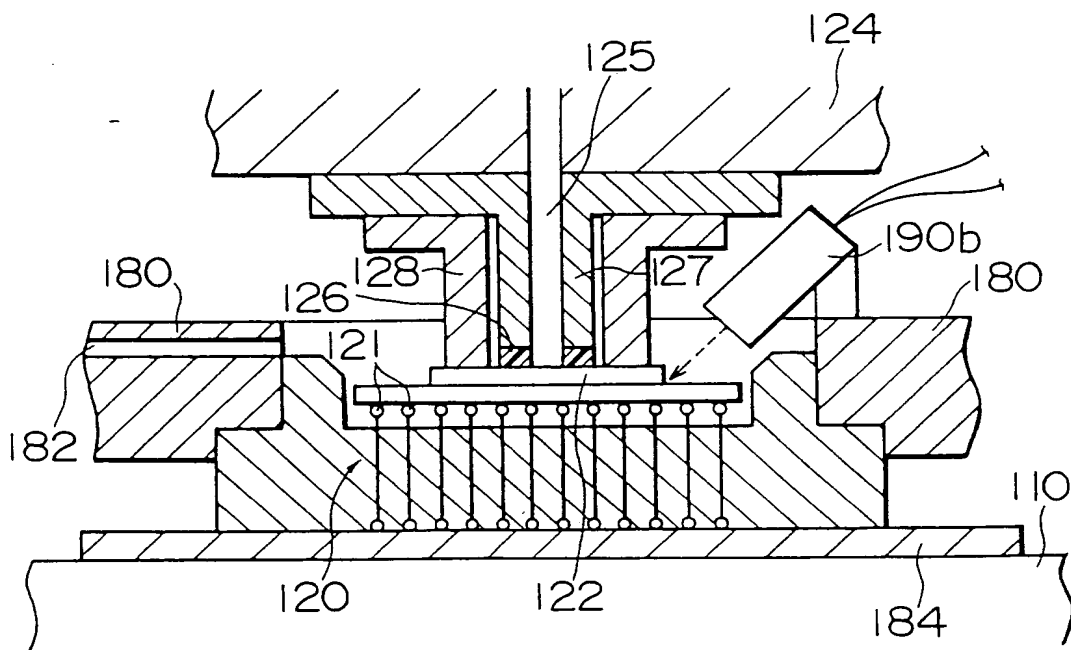
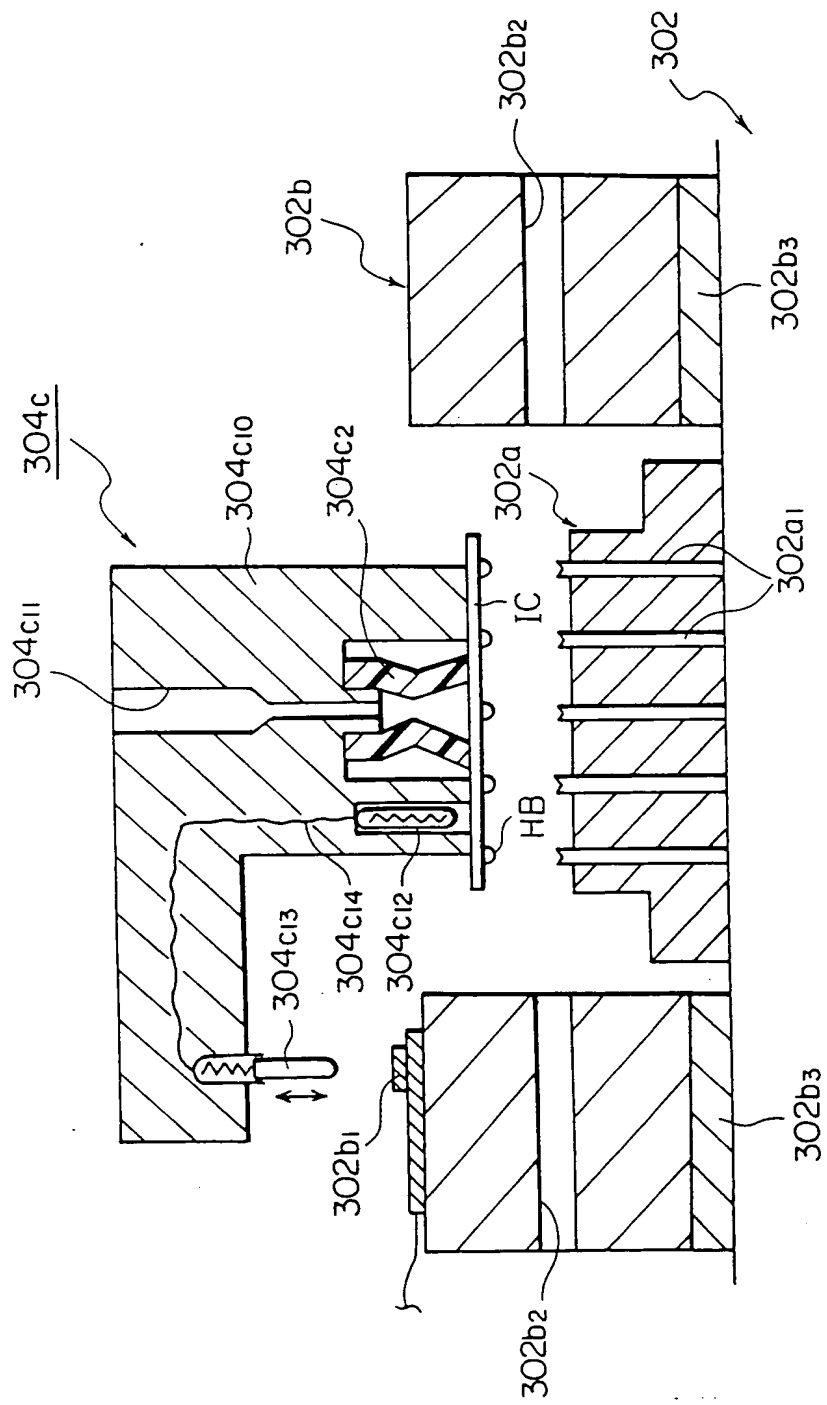


FIG. 9



This cross-sectional view shows a substrate 110 with a base layer 184. A series of vertical structures 120, 122, 124, 125, 126, 127, 128, 180, 182, 190c are formed on the base layer. A dashed arrow indicates a direction of movement or force.

FIG. 11



This cross-sectional view shows a semiconductor device. A central integrated circuit (IC) is mounted on a substrate. The substrate consists of several layers: a bottom layer (302a1), a middle layer (302b1), and a top layer (302b2). A thin layer (302b3) is also present. A top layer (304c) covers the device, featuring openings (304c10, 304c11) and conductive paths (304c12, 304c13, 304c14). The device is shown in a cross-section with hatching indicating different materials.

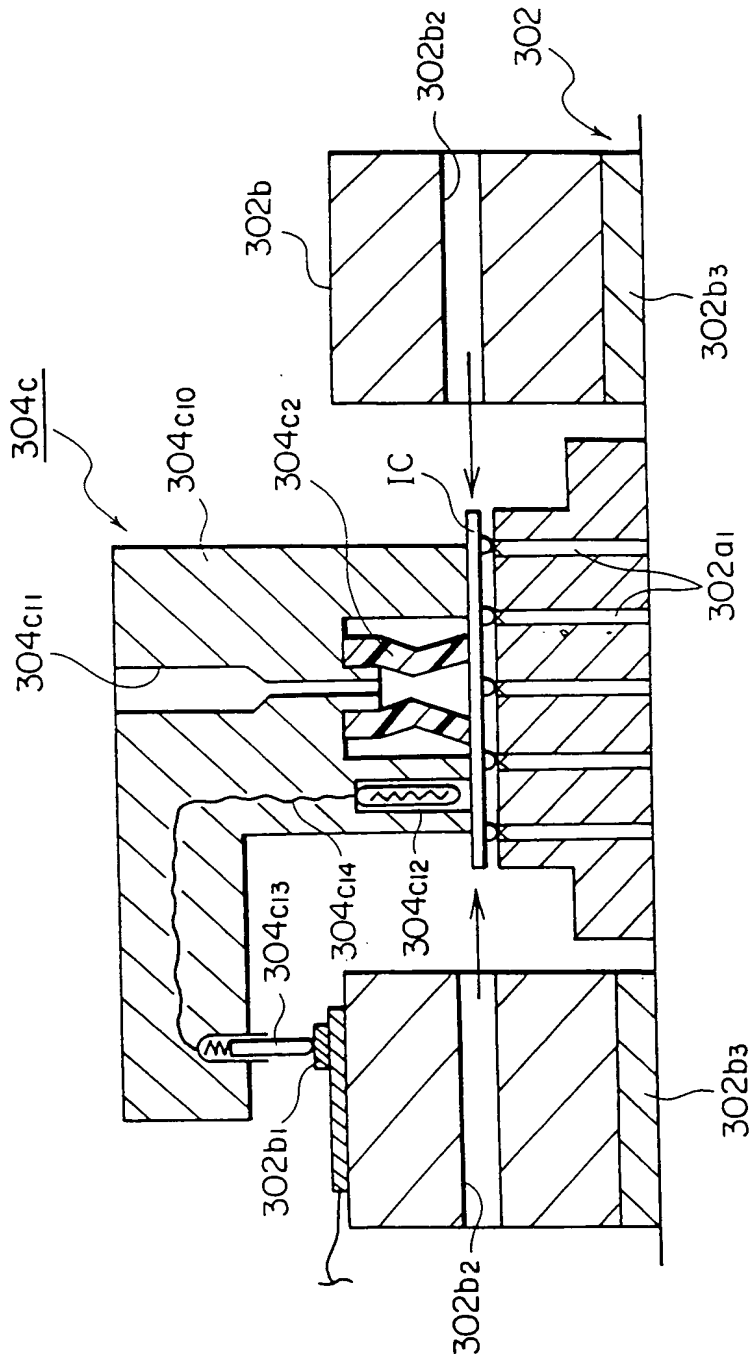


FIG. 13

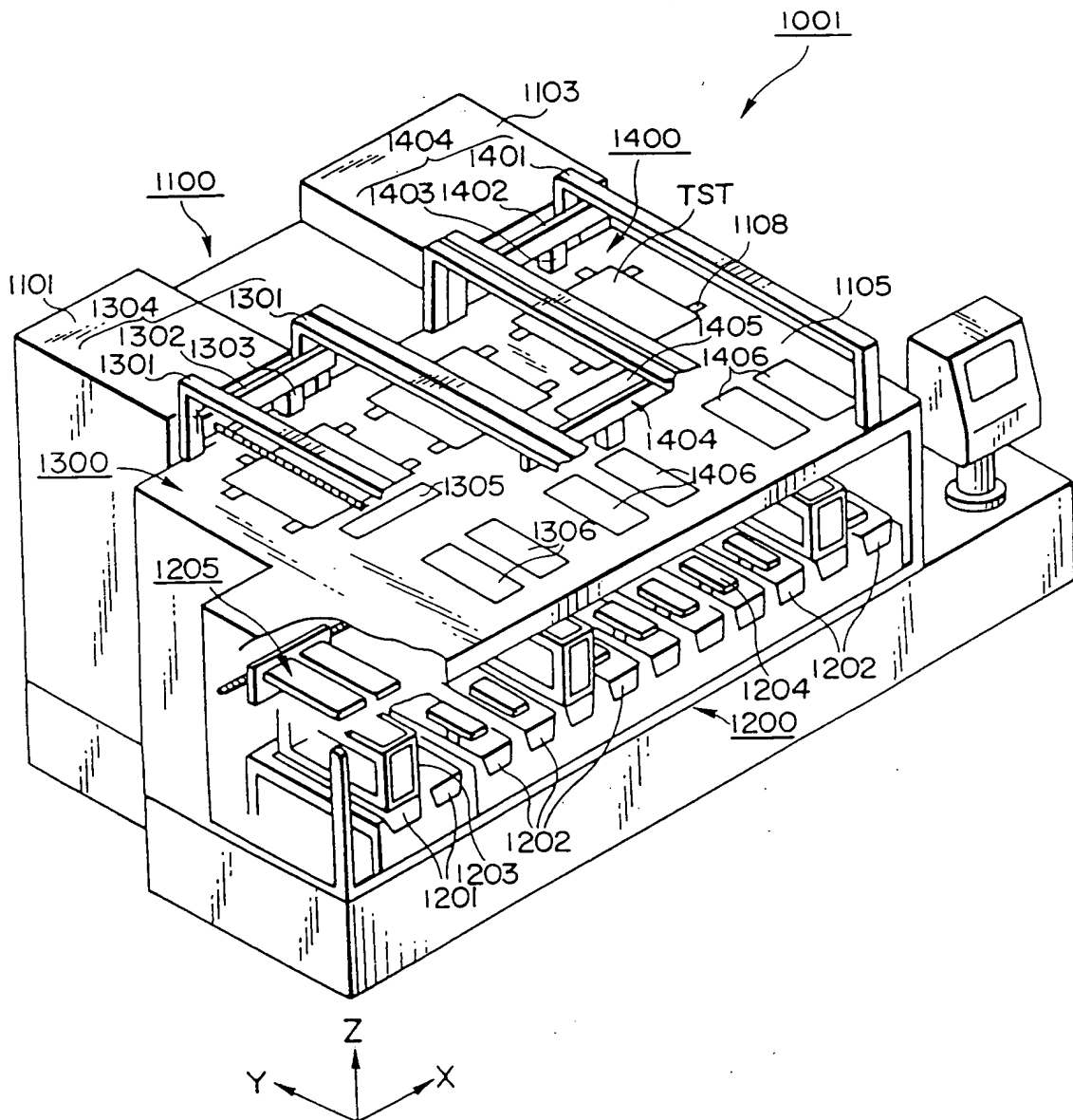


FIG. 14

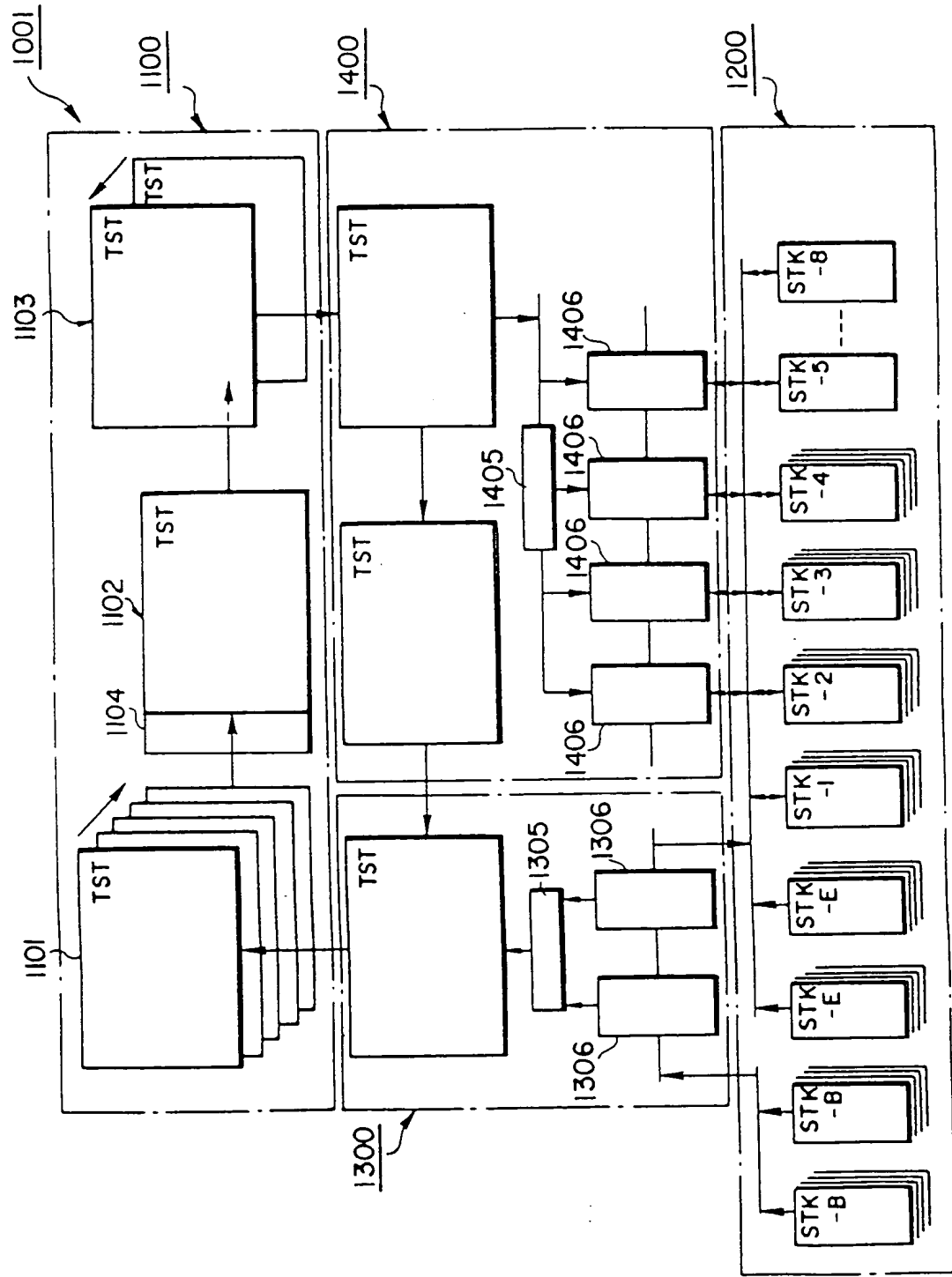


FIG. 15

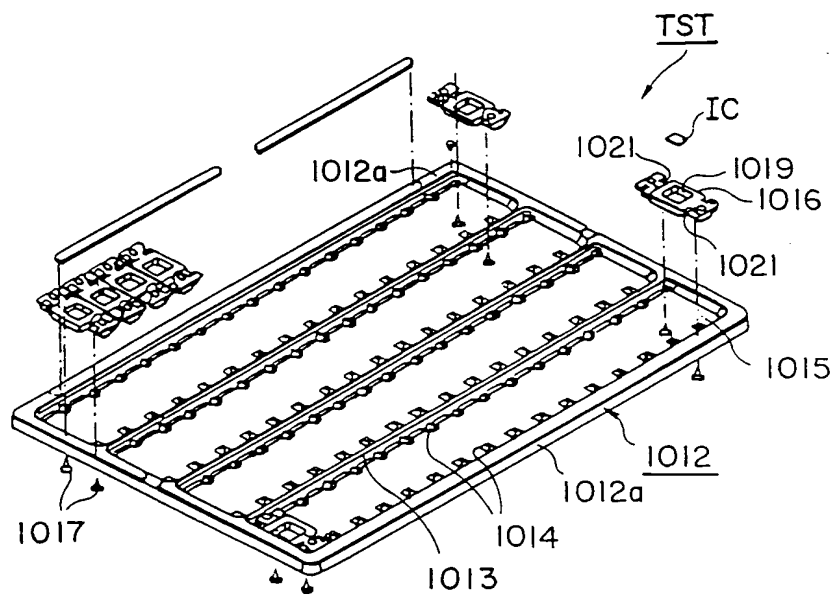


FIG. 16

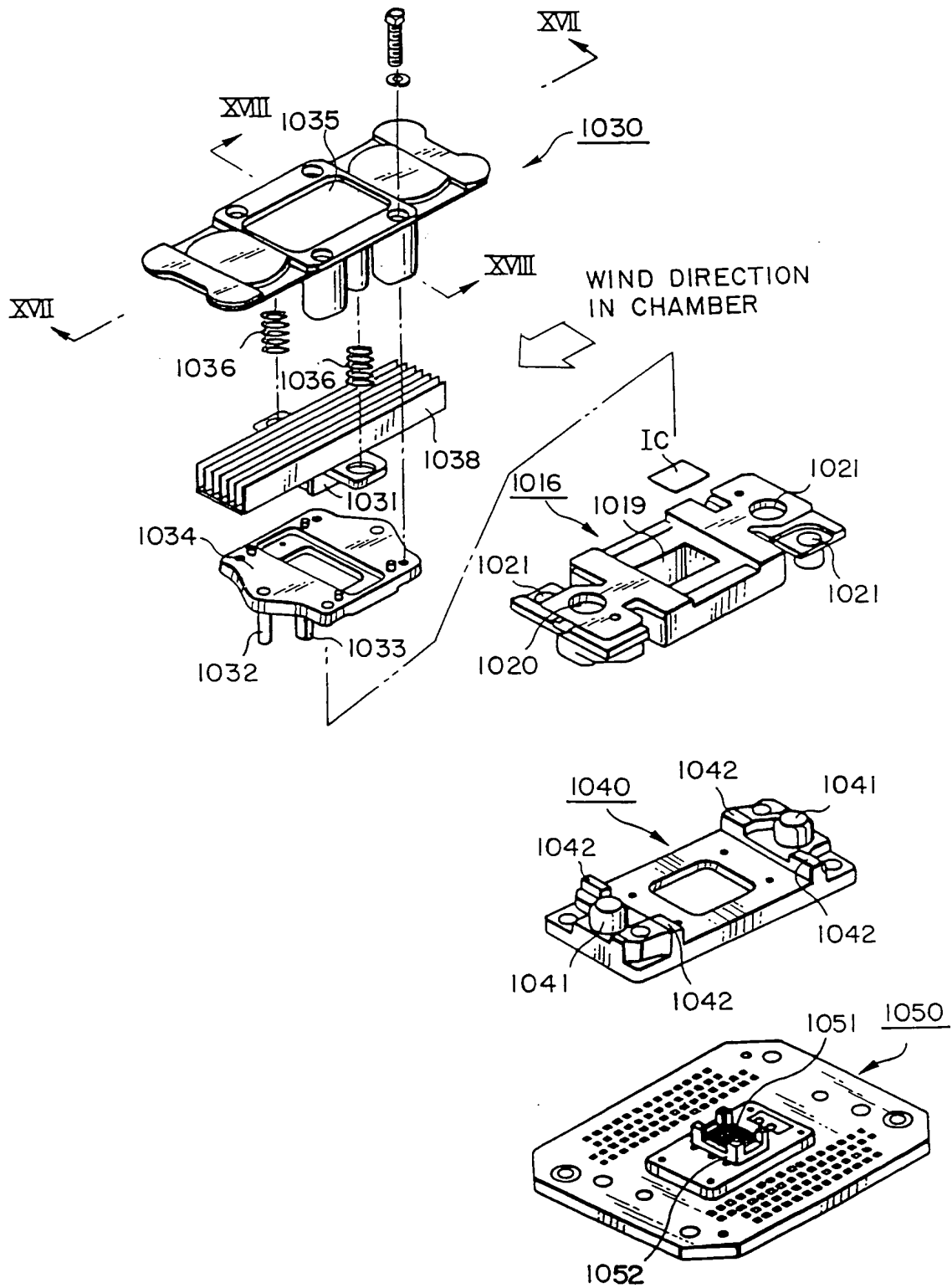


FIG. 17

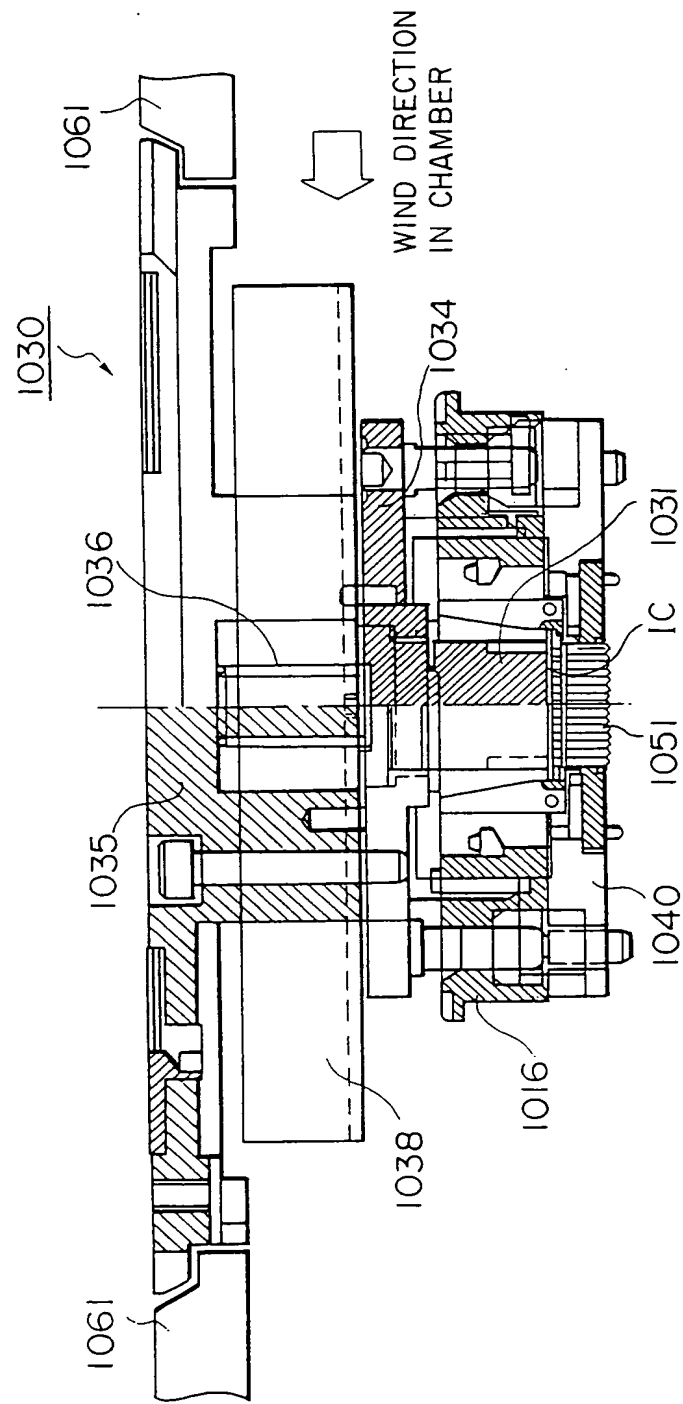


FIG. 18

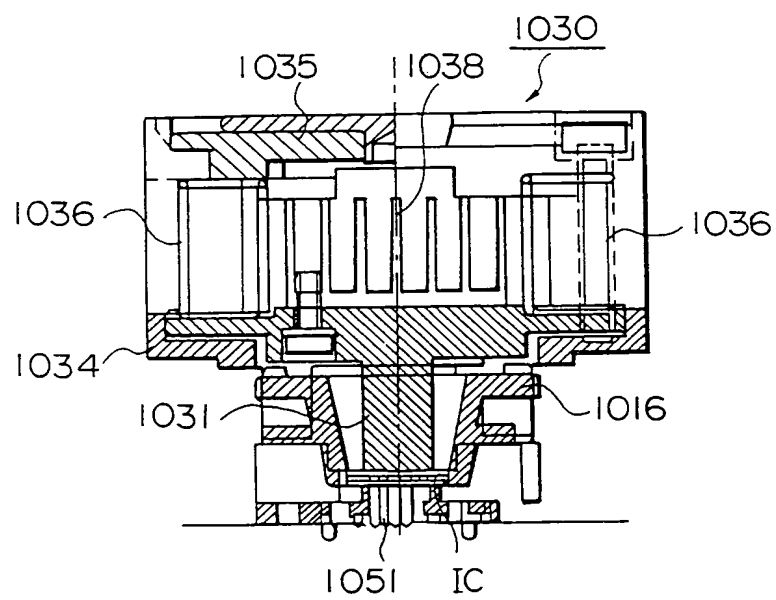


FIG. 19

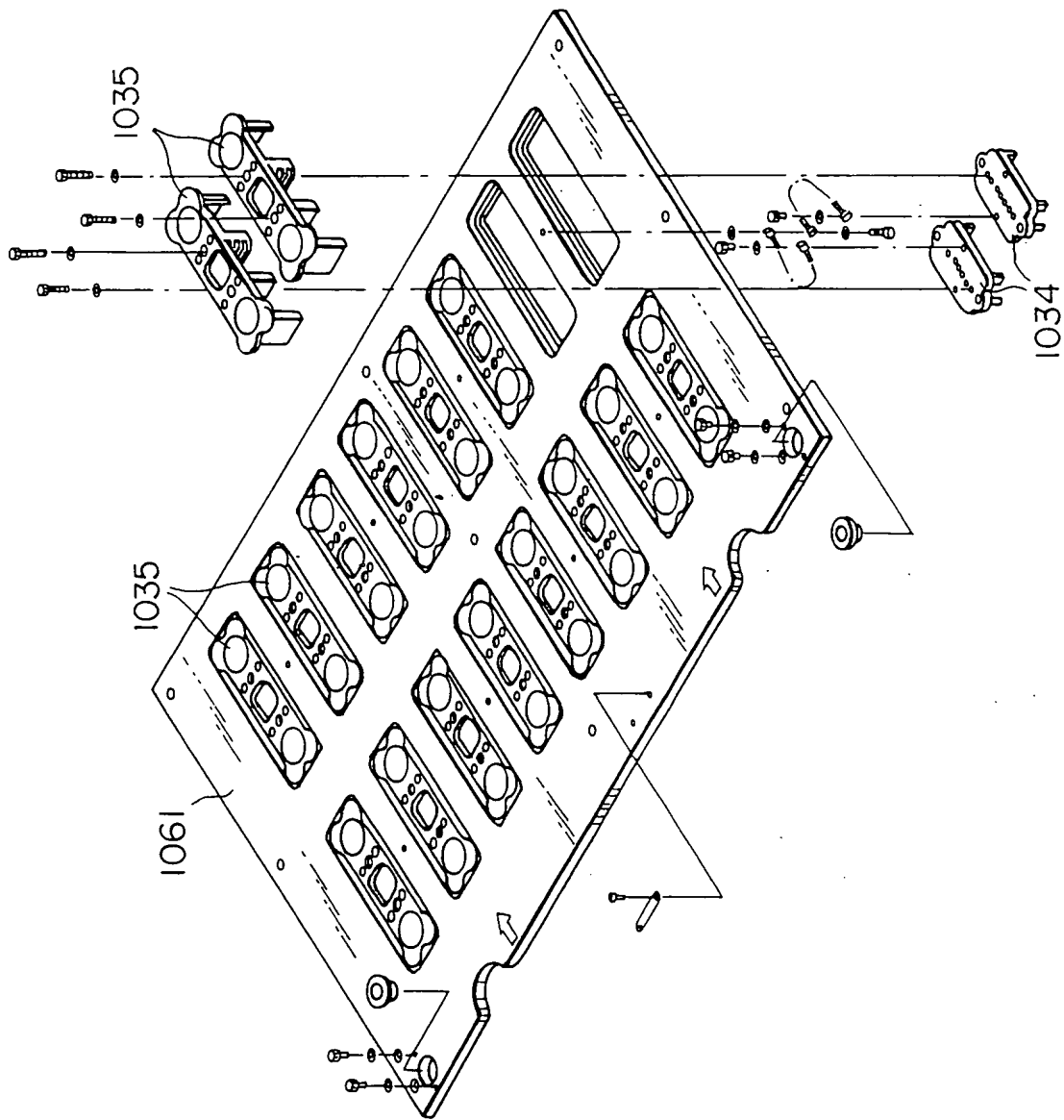


FIG. 20

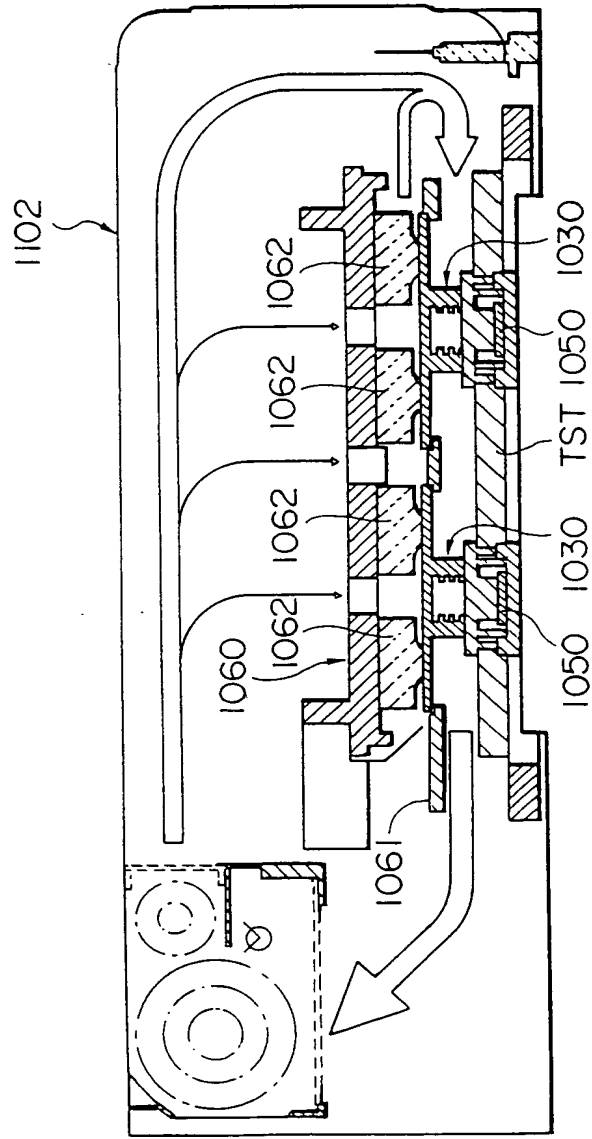


FIG. 21

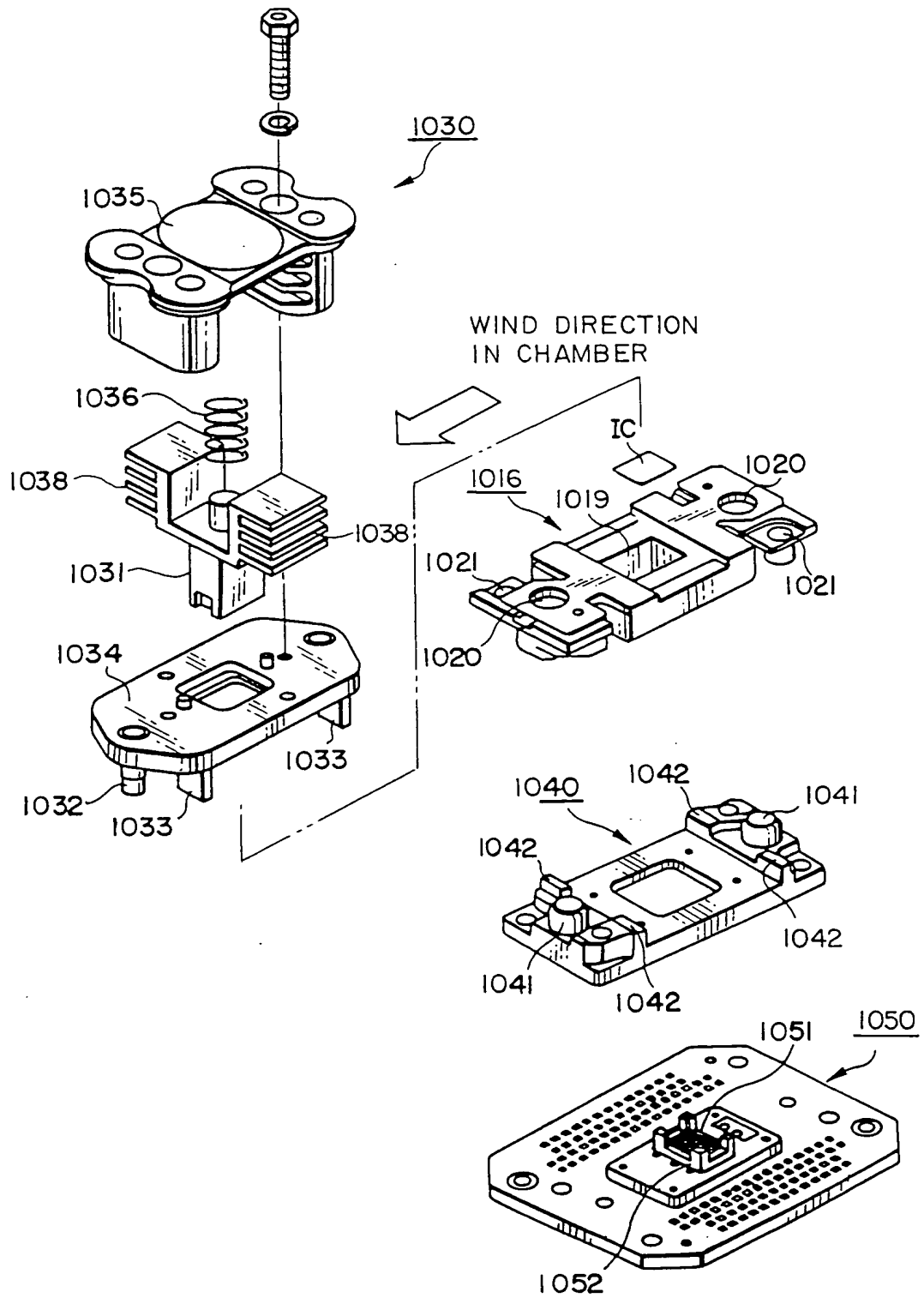


FIG. 22

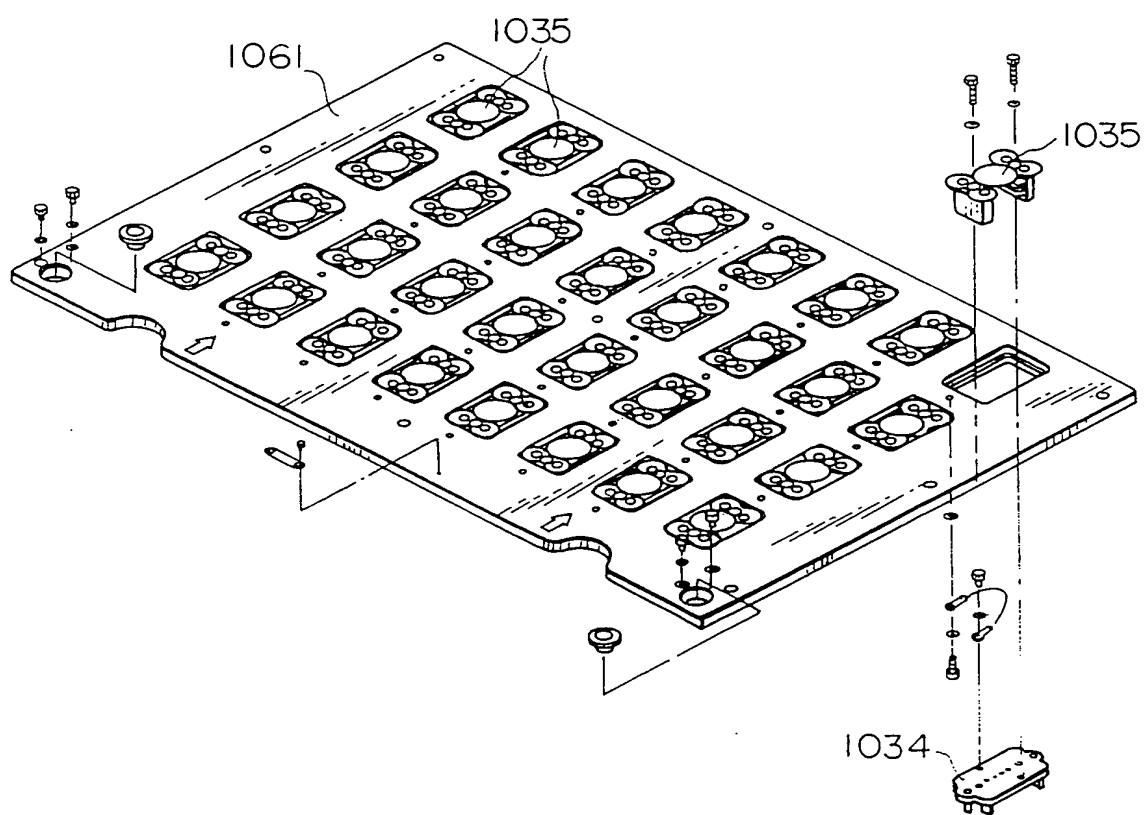


FIG. 23

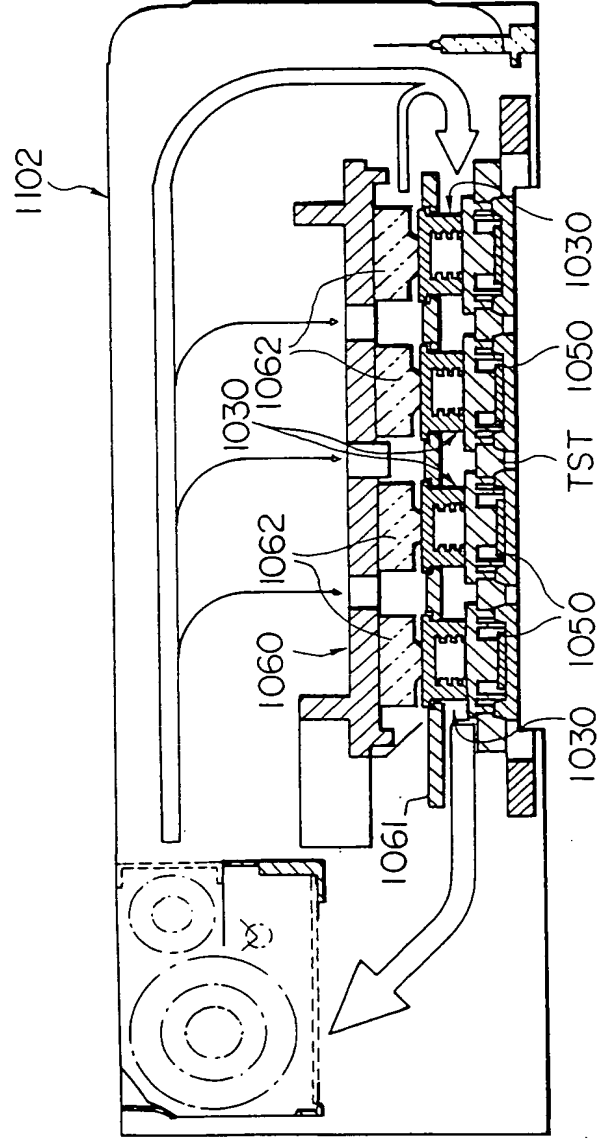


FIG. 24

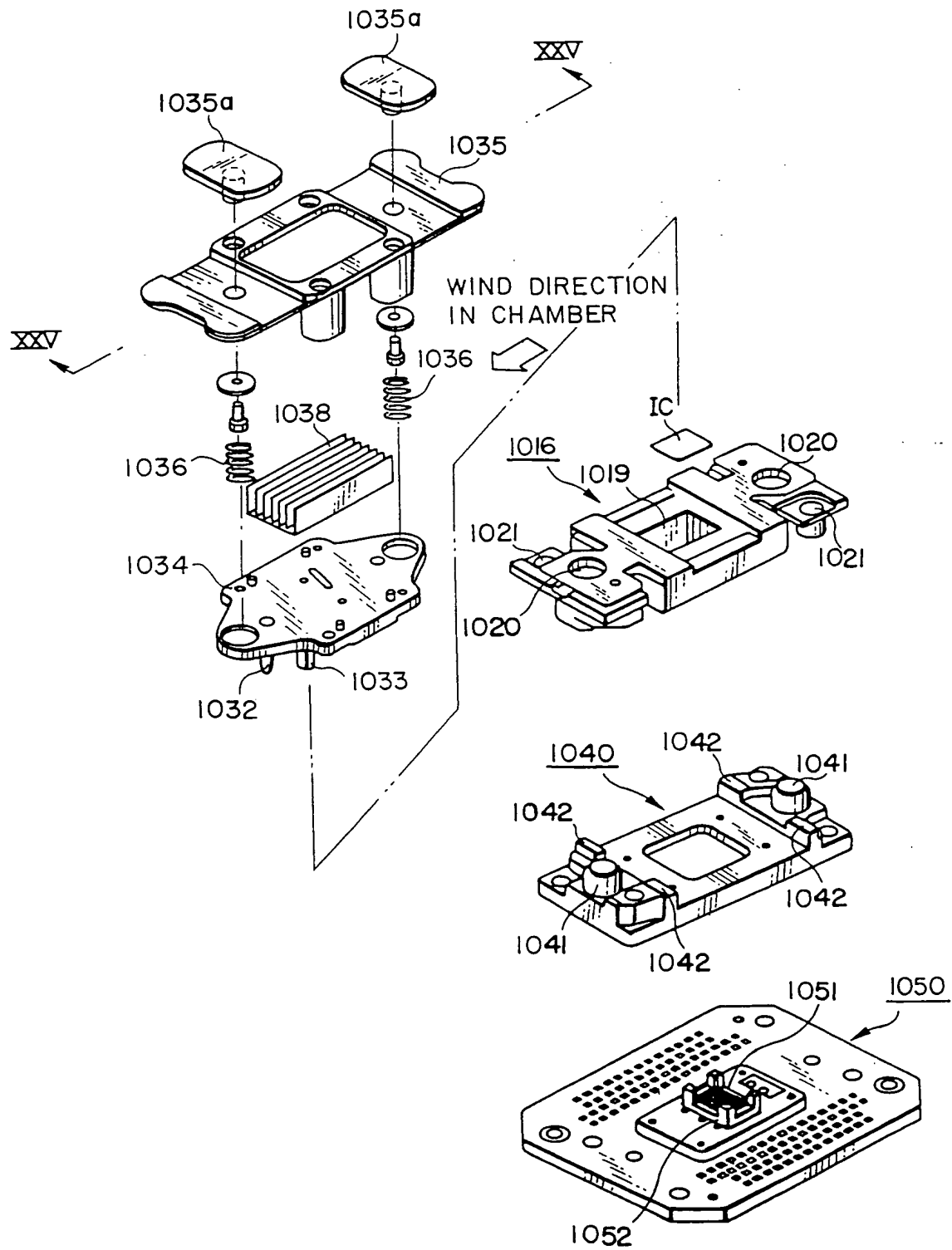


FIG. 25

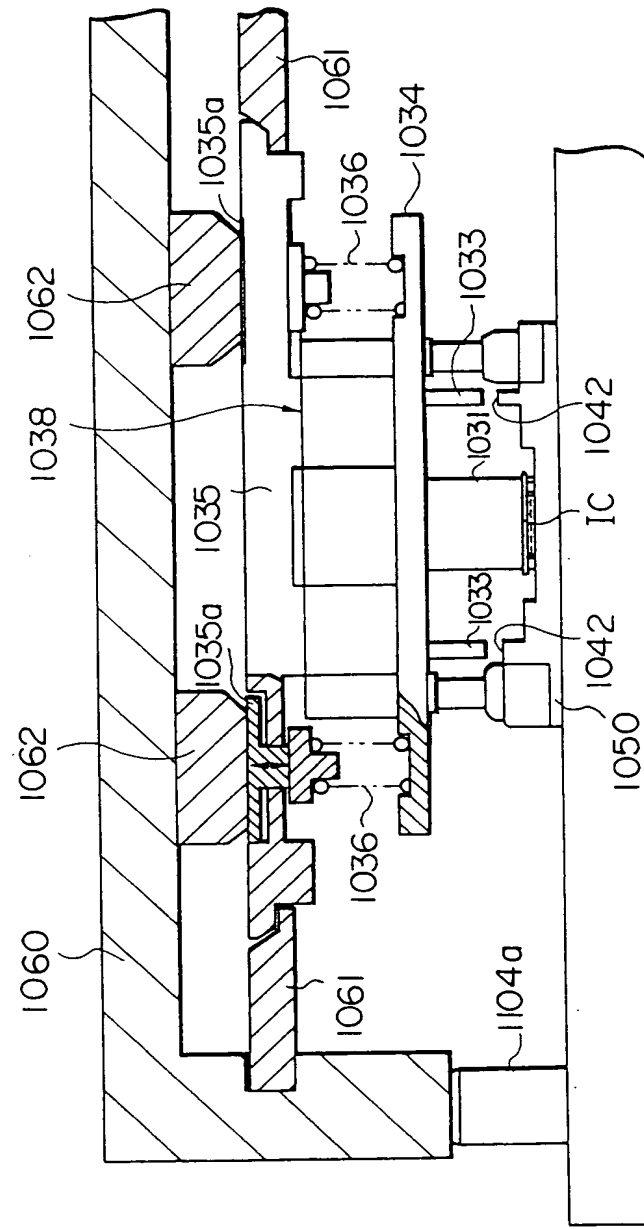


FIG. 26

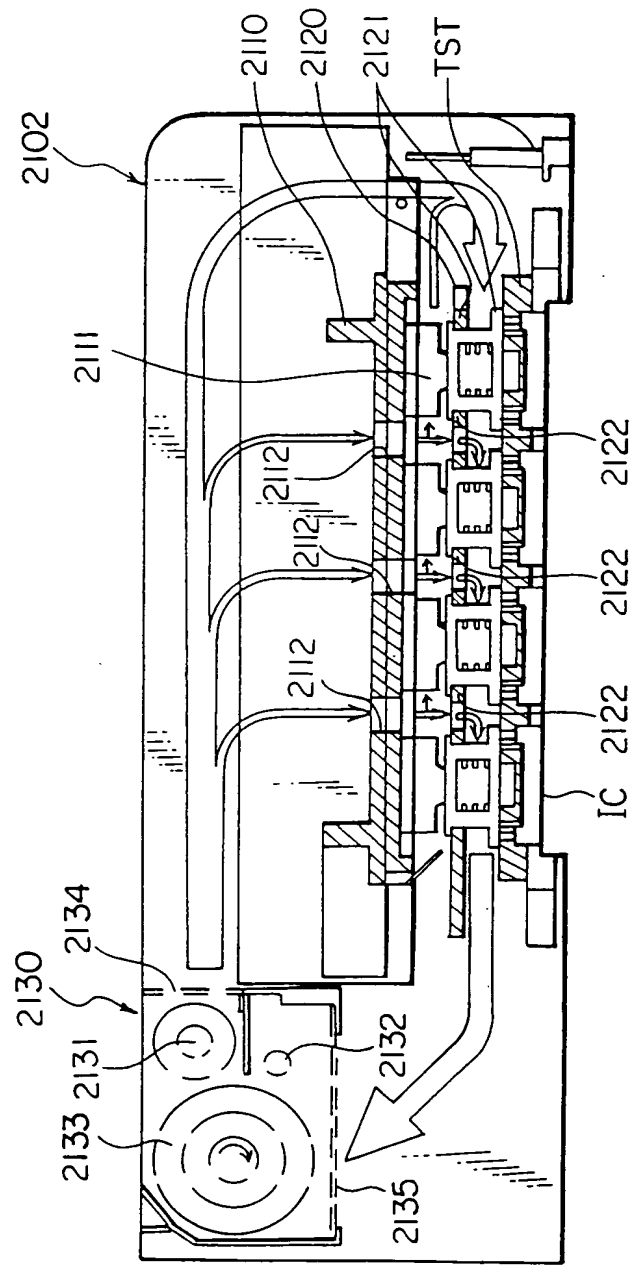


FIG. 27

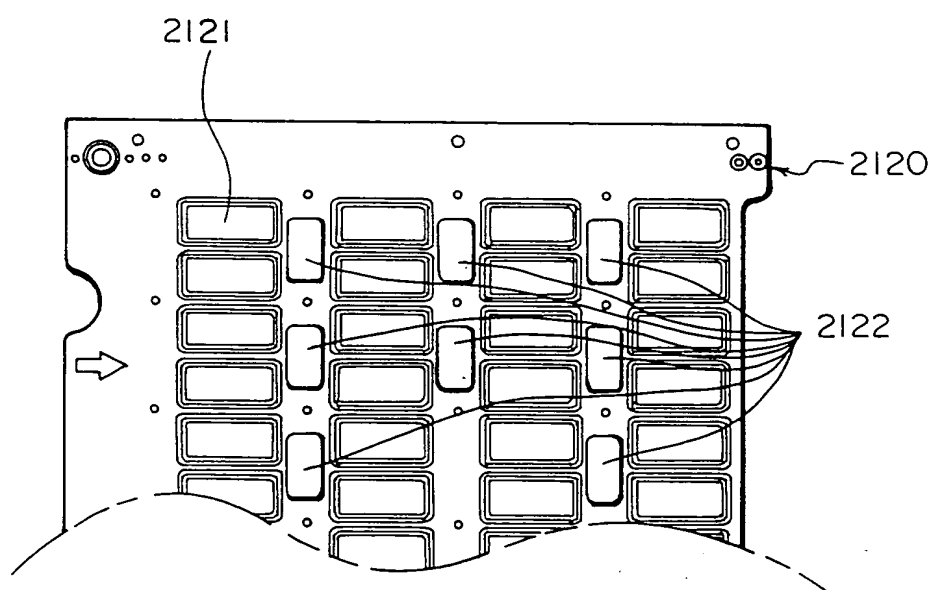


FIG. 28

